## **ABSTRACT**

A reading method for a nonvolatile memory device, wherein the gate terminals of the array memory cell and of the reference memory cell are supplied with a same reading voltage having a ramp-like pattern, so as to modify their current-conduction states in successive times, and the contents of the array memory cell are determined on the basis of the modification order of the current-conduction states of the array memory cell and of the reference memory cell.

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